

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

Claim 1 (original): A semiconductor device comprising:
a semiconductor layer over an insulating surface;
a gate insulating film on said semiconductor layer; and
a gate electrode on said gate insulating film,
wherein said semiconductor layer comprises a channel formation region, at least one LDD region in contact with said LDD region,
wherein said gate electrode has a taper shape, and
wherein said gate electrode comprises a laminate of a fourth electrode, a fifth electrode and a sixth electrode.

Claim 2 (currently amended): A semiconductor device comprising:
a semiconductor layer over an insulating surface;
a gate insulating film on said semiconductor layer; and
a gate electrode on said gate insulating film,
wherein said semiconductor layer comprises a channel formation region, at least one LDD region in contact with said channel formation region, and one of a source region and a drain region in contact with said LDD region,
wherein said LDD region comprises **[[a]]** an impurity region for giving one conductivity at a concentration of 1×10^{17} to $1 \times 10^{20} / \text{cm}^3$, and one of said source region and said drain region comprises said impurity element at a concentration of $1 \times$ **[[1020]]** 10^{20} to $1 \times 10^{21} / \text{cm}^3$
wherein said gate electrode has a taper shape, and
wherein said gate electrode comprises a laminate of a fourth electrode, a fifth electrode and a sixth electrode.

Claim 3 (original): The semiconductor device as claimed in claim 1, wherein said fourth electrode is formed of a conductive film comprising tungsten or a material including tungsten as its main component, said fifth electrode is formed of a conductive film comprising aluminum or a material including aluminum as its main component, and said sixth electrode is formed of a conductive film comprising titanium or a material including titanium as its main component.

Claim 4 (original): The semiconductor device as claimed in claim 2, wherein said fourth electrode is formed of a conductive film comprising tungsten or a material including tungsten as its main component, said fifth electrode is formed of a conductive film comprising aluminum or a material including aluminum as its main component, and said sixth electrode is formed of a conductive film comprising titanium or a material including titanium as its main component.

Claim 5 (original): The semiconductor device as claimed in claim 1, said fourth electrode is overlapped with said LDD region through said gate insulating film.

Claim 6 (original): The semiconductor device as claimed in claim 2, said fourth electrode is overlapped with said LDD region through said gate insulating film.

Claims 7-24 (canceled)

Claim 25 (original): The semiconductor device as claimed in claim 1, wherein said semiconductor device is selected from the group consisting of a computer, a video camera, a digital camera, a mobile telephone, and a projector.

Claim 26 (original): The semiconductor device as claimed in claim 2, wherein said semiconductor device is selected from the group consisting of a computer, a video camera, a digital camera, a mobile telephone, and a projector.